Kurukshetra University, Kurukshetra

(Established by the State Legislature Act-XII of 1956) ("A++" Grade, NAAC Accredited)



Syllabus for

Post Graduate Programme

M.Sc Electronic Science

3rd & 4th Semester

as per NEP 2020 Curriculum and Credit Framework for Postgraduate Programme

With CBCS-LOCF
With effect from session 2025-2026

DEPARTMENT OF ELECTRONIC SCIENCE FACULTY OF SCIENCE

KURUKSHETRA UNIVERSITY, KURUKSHETRA -136119 HARYANA, INDIA

w.e.f. session 2025-26					
Part A - Introduction					
Name of Programme	M.Sc. Electronic Science				
Semester	Third				
Name of the Course	MOS Solid State Circuits				
Course Code	M24-ELE-301				
Course Type	CC-9				
Level of the course	500-599				
Pre-requisite for the course	M24-ELE-101				
Course Learning Outcomes (CLO)	CLO 1 : Describe the working principals of basic building blocks of digital systems				
After completing this course, the learner will be able to:					
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30 0 30				
End Term Exam Marks	70 0 70				
Max. Marks	100	0	100		
Examination Time	3 hours	3 hours			

Unit	Topics	Contact	CLOs
		Hours	
I	Basic digital building blocks, NMOS inverter and its sizing rules, single input NMOS NOR and NAND logic circuits, CMOS inverters, CMOS NOR logic gate, CMOS NAND logic gate, power dissipation, CMOS AND NMOS power dissipation, latch-up and its prevention, signal propagation delays, ratio-logic models, inverter pair delay, NMOS,NAND and NOR delays, CMOS logic delays.voltage.	15	CLO1
II	Dynamic MOS storage circuits, dynamic charge storage, simple shift register, clocked CMOS logic, dynamic RAM memory, register storage circuits, datapath operators, bitparallel adders, bit-serial adders, carry-save addition, pipelining, pipeline architecture, Floor planning methods, block placement and channel definition, routing, power distribution.		CLO2
III	Layout Design rules, resistance estimation, capacitance estimation, MOS capacitor characteristics, MOS device capacitances, diffusion capacitances, single wire capacitance, capacitance design guide, inductance estimation, analytical delay models, gate delay model, power dissipation, static and dynamic power dissipation, shortcircuit dissipation, total power dissipation.	16	CLO3
	CMOS tests methods, need for testing, functionality tests, manufacturing		
IV	tests and principles, fault models, stuck-at faults, short-circuit and open- circuit faults, Automatic test pattern generation, geometrical specification	14	CLO4

languages, parameterized layout representation, graphical symbolic layout, layout equation symbology, design rule checks, digital circuit simulation,		
logic level simulation, switch level simulation, RTL level simulation.		
Total Contact Ho	ours	60

Recommended Books/e-resources/LMS:

- 1. VLSI Design Techniques for Analog and Digital Circuits by Randall L. Geiger, Phillip E. Allen and Noel R. Strader, McGraw-Hill.
- 2. Principles of CMOS VLSI Design- A System Perspective by Neil H.E. Weste and Kamrin Eshraghin, Second Edition, Addison-Wesley.
- 3. Modern VLSI design System –on-Chip Design by Wayne Wolf, PHI, Third Edition.
- 4. Fundamentals of Digital Logic Design by Pucknell (P.Hall)

Outcomes		Internal Assessment (30 Marks)		End Semester Examination (70 Marks)
	Mid Term	Seminar/Presentation/	Class	SEE
	Exam	Assignment/Quiz/Test	Participation	
Marks:	15	10	5	70
CLO1	5	-	-	15
CLO2	5	2.5	-	20
CLO3	5	2.5		20
CLO4		5		15

	w.e.f. Session: 2025-	26			
Part A - Introduction					
Name of Programme	M.Sc. Electronic Science				
Semester	Third				
Name of the Course	Optoelectronics & Microwa	ave Devices			
Course Code	M24-ELE-302				
Course Type	CC-10				
Level of the course	500-599				
Pre-requisite for the course	NIL				
Course Learning Outcomes (CLO)	CLO1: Explain the basic microwave parameters and working of passive and active components.				
After completing this course, the learner will be able to:					
		tum well based devices the works and fibers used in fibre- optic	ng of		
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30 0 30				
End Term Exam Marks	70 0 70				
Max. Marks	100	0	100		
Examination Time	3 hours				

Unit	Topics	Contact Hours	CLOs
I	Microwave Introduction, Waveguides, Rectangular Waveguides - excitation of modes, power transmission, power losses, Microwave parameters-cut off frequency, Characteristic Impedance, Attenuation constant, Phase, Reflection Coefficient, SWR, Power. Microwave passive components (brief)-discontinuities, bands, flanges, TEE's, directional coupler, matched load, attenuators, phase shifter, transitions, ferrite components, slotted line, Wavemeter. Measurements of wavelength, Frequency, impedance, SWR etc. Rectangular Cavity Resonator, Q of cavity, Reentrant cavities. Klystron-operation, velocity modulation, Reflex Klystron-operation, velocity modulation.	15	CLO1
II	Traveling wave tube (in brief), Planar Triodes. Magnetrons (in brief). Transferred Electron Devices, Gunn Effect diode-operation, Modes of operation, microwave generation, amplification, Avalanche Transit Time Devices (in brief) IMPATT diode, TRAPATT diode, BARITT diode. Parametric Devices & Parametric amplifiers (in brief).	15	CLO2
	Basic principles of light emission in semiconductors, spontaneous		

Hours	Total Contact	60	
IV	Quantum well devices: Quantum well lasers, Quantum well detectors, Integrated Optical detectors, factors limiting performance of integrated detectors. Optical fiber communication-Propagation in Fibers, step index fibers, graded index fibers, multipath dispersion, material dispersion combined effect, Attenuation in optical fibers, Semiconductors PIN photodiode detectors and Avalanche Photodiode Detectors for optical communication application, Optical fiber communication systems.	15	CLO4
III	emission, stimulated emission, lasing, lasing threshold, efficiency of light emission. Semiconductor lasers, the laser diode, basic heterostructure, laser structure, SH lasers, DH lasers, Electro-luminescence, LED materials and construction, LED's structures for optical communication applications. Display devices-liquid crystal displays	15	CLO3

Recommended Books/e-resources/LMS:

- 1. Microwave Devices and Circuits by Samuel Y. Liao (Prentice Hall India).
- 2. Electronic Communication Systems by G. Kennedy (TMH).
- 3. Microwave Engineering by R. Chatterjee.
- 4. Microwave Semiconductor Devices and their Circuit Applications by H.A. Watson (McGraw Hill).
 - 5. Integrated Optics: Theory & Technology (3rd edition) by R.G. Hunsperger.
 - 6. Optoelectronics-An Introduction (2nd edition) by J. Wilson, J.F.B. Hawkes.
 - 7. Optical Communication Systems by John Gowar.

Outcomes	Internal Assessment		End Semester Examination	
		(30 Marks)		(70 Marks)
	Mid	Seminar/Presentation/	Class	SEE
	Term	Assignment/Quiz/Test	Participatio	
	Exam		n	
Marks:	15	10	5	70
CLO1	7.5	-	-	17
CLO2	7.5		-	17
CLO3		5		18
CLO4		5		18

w.e.f. session: 2025-26						
	Part A - Introduction					
Name of Programme	M.Sc. Electronic Science					
Semester	Third					
Name of the Course	Custom Microelectronics & ASIO	Cs				
Course Code	M24-ELE-303					
Course Type	DEC-1					
Level of the course	500-599					
Pre-requisite for the	NIL					
course						
Course Learning Outcomes (CLO)	CLO 1: To differentiate among the different types of approaches to implement circuits on IC					
After completing this course, the learner will be able to:	CLO 2: To differentiate among the different types of ASICs and the process involved in their implementation. CLO 3: To compare various simulation types and delay models.					
the learner will be able to:	CLO 4: To understand the vari					
Credits	Theory	Practical	Total			
	4 0 4					
Teaching Hours per week	4 0 4					
Internal Assessment Marks	30 0 30					
End Term Exam Marks	70 0 70					
Max. Marks	100	100 0 100				
Examination Time	3 hours					

Unit	Topics	Contact	CLOs
		Hours	
I	Microelectronics evolution, why custom microelectronics, Custom microelectronic techniques. Full hand-crafted custom design, fixed cell architectures, soft cell architectures, macrocells, Analog cells, Gate array techniques, sea of gates, Routing considerations.	15	CLO1
П	ASIC design flow, ASIC library design, Programmable ASIC's, ASIC construction, physical design, CAD tools, System partitioning, FPGA partitioning, partitioning methods.	15	CLO2
III	Types of simulation, structural simulation, static timing analysis, Gate level simulation, Net capacitance, Logic systems, cell models, delay models static timing analysis, Formal verification, Switch level simulation, Transistor level simulation.	16	CLO3
IV	Low level design entry, Schematic entry, Floor planning and placement, Floor planning goals and objectives, placement terms and definitions, Goals and objectives physical design flow, Routing: global routing, Detailed routing, Special routing, testing,	14	CLO4
	Importance of testing, Boundary Scan test, Faults, Automatic test pattern generation, Built in self-test, Simple test example		
	Total Cont	act Hours	60

Recommended Books/e-resources/LMS:

- 1. Custom VLSI Microelectronics by Stanley L. Hurst (Prentice Hall 1992)
- 2. Application-Specific Integrated Circuit by Michael John Sebastian Smith (Addison Wesley)
- 3. Application-Specific Integrated Circuit (ASIC) Technology-Academic Press.

Outcomes		Internal Assessment		End Semester
		(30 Marks)		Examination (70 Marks)
	Mid Term	Seminar/Presentation/	Class	SEE
	Exam	Assignment/Quiz/Test	Participation	
Marks:	15	10	5	70
CLO1	5	-	-	15
CLO2	5	2.5	-	20
CLO3	5	2.5		20
CLO4		5		15

w.e.f. Session: 2025-26					
	Part A - Introduction				
Name of Programme	M.Sc Electronic Science				
Semester	Third				
Name of the Course	Foundations of MEMS				
Course Code	M24-ELE-304				
Course Type	DEC-1				
Level of the course	500-599				
Pre-requisite for the course (if any)					
comes (CLO)	CLO 1: Ability to understand the multidisciplinary nature, components, need, principle of operation and applications of MEMS CLO 2: Ability to understand various sensing and actuation mechanism used in MEMS devices and compare their merits and demerits. CLO 3: Ability to understand the choice of material and fabrication processes for MEMS CLO 4: Ability to design the MEMS device for specific application and simulate design using MEMS design tools Theory Practical Total				
	4	0	4		
Teaching Hours per week	4 0 4				
Internal Assessment Marks	30 0 30				
End Term Exam Marks	70 0 70				
Max. Marks	100	0	100		
Examination Time	3 hours				

Unit	Topics	Contact	CLOs
Ţ	MEMS & Migrosystam Definition Typical MEMS and	Hours 15	CLO1
1	MEMS & Microsystem- Definition, Typical MEMS and Microsystems Products Microsystems vs MEMS, Microsystems vs Microelectronics, Multidisciplinary nature of Microsystem design and Manufacture, Why miniaturization? Intergrated Microsystems:-Micromechanical Structures, Microsensors, Microactuators, Applications of MEMS and Microsystems Sensors and Actuators: Energy Domains and Transducers, Sensor Consideration, Actuator Considerations, Scaling in MEMS (Ref-2)	13	CLOT
II	Scaling laws in Miniaturisation: Scaling in Geometery, Rigid Body Dynamics, Electrostatics forces, Magnetostatic Forces, Fluid Mechanics, Heat transfer, Diffusion and Electricity Working principles of MEMS: Microsensors: Pressure sensor, Thermal sensors, Optical Sensors,	15	CLO2
	Chemical Sensors, Biosensors, Acoustic Wave Sensors Microactuation: Actuation using thermal forces, piezoelectric		

N	rystals, Shape Memory Alloys and Electrostatic forces Iicroactuators : Microgripper, micromotor, microvalves and nicropumps		
M	Aicro-accelerometer and microfluidics		
III N	Aicromachining Technologies :	15	CLO3
m Si Pi M pr et G	Microfabrication and Material for MEMS: Si as substrate material, nechanical properties of Silicon, Silicon Compounds (SiO ₂ , Si ₃ N ₄ , iC, polySi, Silicon), Piezoresistors, Piezoelectric crystals, olymers, Packaging Materials. Micromachining Processes: Overview of microelectronic fabrication rocesses used in MEMS, Bulk Micromachining, Anisotropic wet tching, DRIE, Etch stop techniques, Surface Micromachining – General description, Case studies using MEMS Design Tools		
	ntergration of Micro and Smart Systems	15	CLO4
	ntergartion of Microsystems and Microelectronics : CMOS		
	First, MEMS First, Other Integration Approaches		
	Microsystems Packaging: Objectives of Packaging, Special issues		
	n Microsystems Packaging, Types of Microsystem Packaging, ackaging technology,		
	Case study of Pressure Sensor and Micromachined Accelerometer as		
	ntegrated Microsystems . Case study of PZT Transducer and		
	Tibrations in Beam as a smart structure in Vibration Control		
	Total Contact Hours	60	

Recommended Books/e-resources/LMS:

- 1. Foundations of MEMS, Liu, Pearson India
- 2. Microfabrication by Marc Madao, CRC Press
- 3. MEMS & Microsystems Design and Manufacture by Tai-Ran H Su, Tata Mcgraw
- 4. Microsystem Design by S.D. Senturia, Ruiwer Academic Publisher
- 5. Micro and Smart Systems by Anathasuresh et. Al., Wiley India

Outcomes	Internal Assessment (30 Marks)			End Semester Examination (70 Marks)
	Mid Term	Seminar/Presentation/ Assignment/Quiz/Test	Class Participation	SEE
	Exam		•	
Marks:	15	10	5	70
CLO1	5	2.5	-	17
CLO2	5	2.5	-	17
CLO3	2.5	2.5		18
CLO4	2.5	2.5		18

w.e.f. Session: 2025-26						
Part A - Introduction						
Name of Programme	M.Sc. Electronic Science					
Semester	Third					
Name of the Course	Advanced Semiconductor I	Manufacturing				
Course Code	M24-ELE-305					
Course Type	DEC-1					
Level of the course	500-599					
Pre-requisite for the course	M24-ELE-102: IC Fabricatio	n Technology				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	fabrication technology					
Credits	Theory	Practical	Total			
	4 0 4					
Teaching Hours per week	4	0	4			
Internal Assessment Marks	30 0 30					
End Term Exam Marks	70 0 70					
Max. Marks	100 0 100					
Examination Time	3 hours					

Unit	Topics	Contact Hours	CLOs
I	Wafer shaping process cleaning mechanical properties of the wafer, Silicon wafer criteria for VLSI/ULSI technology, High technology silicon wafer concept, VLSI/ULSI wafer characteristics, structural and chemical and mechanical characteristics.	15	CLO1
II	Silicon nitride, nitride properties of silicon nitride, plasma-assisted deposition, deposition variable, properties of plasma assisted deposited filing, other material, stability and semiconductor and insulating, patterning, Self-aligned silicides.	15	CLO2
III	materials for contacts and interconnects, Metallization, Applications, gates and interconnections, Ohmic contacts, Metallization choices, Metals or allays properties, Metallization problem, metallurgical and chemical interactions, electro-migration, new role of metallization, multilevel structures, epitaxial metals, diffusion barriers and redundant metal links	16	CLO3
IV	Assembly and packaging of VLSI devices package types, packaging design considerations, thermal design considerations, electrical considerations, mechanical design considerations, VLSI assembly technologies, wafer preparation, die-banding, wire bonding, package fabrication technologies ceramic package, glass-sealed refractory package, plastic molding	14	CLO4

technology molding process, special package considerations.			
	Total Contact	Hours	60
Part C-Learning Resources			
Recommended Books/e-resources/LMS:			
1. Semiconductor Silicon Crystal Technology, Fumio Shimura, acader	mic Press, Inc.		
2 VI SI Technology SM Sze McGraw Hill International Ed			

Outcomes	Internal Assessment (30 Marks)			End Semester Examination (70 Marks)
	Mid Term	Seminar/Presentation/	Class	SEE
	Exam	Assignment/Quiz/Test	Participation	
Marks:	15	10	5	70
CLO1	5	-	-	15
CLO2	5	2.5	-	20
CLO3	5	2.5		20
CLO4		5		15

w.e.f. session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc Electronic Science				
Semester	Third				
Name of the Course	Digital Communication				
Course Code	M24-ELE-306				
Course Type	DEC-1				
Level of the course	500-599				
Pre-requisite for the course (if any)					
Course Learning Outcomes	CLO 1: Ability to understand n	need and application	ns of the Digital Com-		
(CLO)	munication		_		
	CLO 2: Ability to Understand	the design and perfo	ormance parameters of		
the learner will be able to:	component blocks	. 11 17 1	1 1		
	CLO 3: Ability to understand v	arious digital modu	ilation and error correc-		
	tion techniques CLO 4: Ability to Understand t	tha diaital tuanamia	sion of Analog signals		
Con dita			<u> </u>		
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30 0 30				
End Term Exam Marks	70 0 70				
Max. Marks	100	0	100		
Examination Time	3 hours	_			

Unit	Topics	Contact	CLOs
		Hours	
I	Unit I	15	CLO1
	Introduction: Model of Communication System, Elements of a Digital		CLO2
	Communication System, Analysis and Design of Communication		
	System, Classification of Signals and Systems		
	A brief review of Random Signal Theory: Probabilities, Random		
	Variables and Random Processes		
	Information and Channel Capacity: Measure of Information,		
	Encoding of the Source output - Shannon Encoding Algorithm and		
	Huffman Encoding algorithm (Ref. 3), Discrete Communication		
	Channels: Only Memoryless, Continuous Communication Channel:		
	Shannon- Hartley Theorem		
II	Digital Modulation Techniques: Introduction, Binay Phase-Shift Keying,	15	CLO3 CLO3
	Differential Phase-Shift Keying, Differentially- Encoded PSK, Quardrature Phase Shift Keying, M-ary PSK, Quadrature Amplitude Shift Keying, Bina-		0200
	ry FSK, Similarity of BFSK and BPSK, M-ary FSK, Minimum Shift Key-		
	ing, Duobinary Encoding, A Comparison of Narrowband FM System (Ref		
	2)		
III	Error control coding: Examples of Error control coding, Methods of	15	CLO3
	controlling errors, Types of errors and codes, Linear block codes,		CLO4

Binary cyclic codes. Convolutional Codes-Trellis Code		
IV Digital Transmission of Analog Signals, Sampling theory and	15	CLO4
Practice, Quantizing of Analog Signals, , PCM, Delta Modulation, Q-		
level differential PCM, Time Division		
Multiplexing, Spread Spectrum and Multiple Access Techniques,		
Introduction to Spread Spectrum Modulation, Code Acquisition and		
Tracking, Spread Spectrum as a Multiple Access Techniques.		
Total Contact Hours	60	

Recommended Books/e-resources/LMS:

- 1. Digital and Analog Communication Systems by K. Sam Shanmugan (John wiley & Sons 1994).
- 2. Principles of Communication System by Taub and Schilling (McGraw Hill International).
- 3. An Introduction to Analog & Digital Communication by Simon Haykin.
- 4. John G.Proakis, "Digital Communication" McGraw Hill 3rd Edition, 1995

Evaluation N	remou			
Outcomes		Internal Assessment		End Semester Examination
		(30 Marks)		(70 Marks)
	Mid	Seminar/Presentation/	Class	SEE
	Term	Assignment/Quiz/Test	Participation	
	Exam			
Marks:	15	10	5	70
CLO1	5	2.5	-	17
CLO2	5	2.5	-	17
CLO3	2.5	2.5		18
CLO4	2.5	2.5		18

w.e.f. session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc Electronic Science				
Semester	Third				
Name of the Course	Advanced Embedded Systems				
Course Code	M24-ELE-307				
Course Type	DEC-2				
Level of the course	500-599				
Pre-requisite for the course (if any)					
Course Learning Outcomes	CLO 1: Ability to understand r	need and application	ns of 32-bit Embedded		
(CLO)	Systems				
After completing this course,	CLO 2: Ability to analyze give	en problem and writ	te programs using ARM		
the learner will be able to:	assembly and C langua				
	CLO 3: Ability to design interf				
	CLO 4: Ability to understand t				
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30	0	30		
End Term Exam Marks	70	0	70		
Max. Marks	100	0	100		
Examination Time	3 hours				

Unit	Topics	Contact Hours	CLOs
I	32-Bit or Higher Order Processors	14	CLO1
	Intel 80386DX: Architecture, Interrupt Facilities, Instruction Set,		
	80387 floating point co-processor INTEL 80486 : Instruction set		
	Intel 486SX and overdrive processors Intel Pentium: Multiple		
	branch prediction, Data flow analysis Speculative Execution, The		
	MMX instructions Pentium-II		
	Integrated Processors		
	RISC processors ::		
	The Berkeley RISC model ,Sun SPARC RISC processor		
	Architecture		
	Interupts, instruction set, The stanford RISC Model		
	The MPC603 block diagram		
	The ARM : register set, Exceptions, The Thumb instructions		
	Digital signal processors, DSP Basic Architecture, Chossing a		
	Processor		
II	ARM : Architecture and Assembly Language Programming	16	CLO2
	Architecture, Interrupt Vector Table, Programming the ARM Processors		
	ARM Assembly Language, ARM Instruction Set, Conditional Exe-		

	cution Arithmetic Instructions , Logical Instructions , Compare Instructions Multiplication, Division		
III	Starting Assembly Langauge Program General Structure of an Assembly Language, Writing Assembly Programs, Branch Instructions, Loading Constants, Load and Store Instructions, Readonly and Read/Write Memory, Multiple Register Load and Store ARM: Peripheral Programming of ARM MCU using C Block Diagram, Features of the LPC 214x Family Peripherals ARM 9, ARM Cortex-M3	16	CLO2 CLO3
IV	DSP Processors	14	CLO4
	The Application Scenario, General Features of Digital Signal		
	Processors		
	SIMD Techniques ,The SHARC Floating Point Processor ,DSP		
	Processors of Texas Instruments (TI) ,OMAP (Open Multimedia		
	Applications Platform		
	Total Contact Hours	60	

Suggested Evaluation Methods				
Internal Assessment: 30 End Term Examination: 70				
Theory		Theory	70	
Class Participation:	5	Written Examination		
• Seminar/Presentation/Assignment/Quiz/Class test etc.:	10	1		
• Mid-Term Exam:	15	-		

Recommended Books/e-resources/LMS:

- Embedded Systems-An integrated Approach , Layla B. Das, 1st edition Pearson, 2012
 Embedded System Design, Steve Heath, 2nd Edition, Elsevier , 2005
- 3. Introduction to Embedded Systems: Shibu K. V. (TMH

Outcomes	Internal Assessment (30 Marks)			End Semester Examination (70 Marks)
	Mid	Seminar/Presentation/	Class	SEE
	Term	Assignment/Quiz/Test	Participation	
	Exam			
Marks:	15	10	5	70
CLO1	7.5	-	-	17
CLO2	7.5		-	17
CLO3		5		18
CLO4		5		18

w.e.f. Session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc. Electronic Science				
Semester	Third				
Name of the Course	Chip Implementation with	Physical Design			
Course Code	M24-ELE-308				
Course Type	DEC-2				
Level of the course	500-599				
Pre-requisite for the course	Knowledge of MOS Devices & IC Fabrication process				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	CLO 2 : To study about architecture and operations of different				
Credits	Theory Practical Total				
	4 0 4				
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30	0	30		
End Term Exam Marks	70	0	70		
Max. Marks	100 0 100				
Examination Time	3 hours				

Unit	Topics	Contact	CLOs
ı	Introduction to Physical Design and EDA Tools: Introduction to Physical Design SoC Flow. Overview of the complete Physical Design SoC flow. Introduction to EDA Tools. Overview of Synopsys, Cadence, Siemens, and open-source alternatives. Standard Cell and Key Design Elements. Analysis of standard cells and essential design elements. Hands-on exercises using	Hours 15	CLO1
	EDA tools.		
II	Logic & Physical Synthesis and Timing Analysis Logic & Physical Synthesis Application of logic synthesis techniques. Physical synthesis for placement and routing optimization. Timing Constraints and Analysis. Definition and implementation of timing constraints. Analysis of timing characteristics and mitigation strategies.	15	CLO2
≡	Floor Planning, Placement, and Clock Tree Synthesis: Floor Planning and Placement. Development of floor plans for efficient chip layout. Optimization of chip placement for performance and area. Clock Tree Synthesis and Routing. Implementation of clock tree synthesis. Routing techniques for interconnections within the design.	16	CLO3
IV	Timing Closure, Physical Design Verification, and Tape-Out: Timing Closure Techniques. Application of techniques to achieve timing closure. Addressing challenges in meeting timing requirements. Physical	14	CLO4

Design Verification, Tape-Out, and DFT/DFM Introduction: Methods for
physical design verification. Overview of the tape-out process. Introduction
to Design for Testability (DFT) and Design for Manufacturability (DFM)
principles.

Total Contact I	Hours	

60

Part C-Learning Resources

Recommended Books/e-resources/LMS:

- 1. Cem Unsalan, Bora Tar. Digital System Design with FPGA: Implementation using Verilog and VHDL. McGraw-Hill, First Edition.
- 2. Nekoogar, Farzad. From ASICs to SOCs. Prentice Hall Professional, 2003.
- 3. Chakravarthi, Veena. SoC Physical Design. Springer Nature, 2022.
- 4. Kahng, Andrew. VLSI Physical Design: From Graph Partitioning to Timing Closure. Springer Science & Business Media, 2011.
- 5. Michael Keating, Synopsys. The Simple Art of SoC Design. Springer Science & Business Media, 2011.
- 6. Sait, Sadiq. VLSI Physical Design Automation. World Scientific, 1999.

Evaluation internod						
Outcomes	Internal Assessment			End Semester		
	(30 Marks)			Examination (70 Marks)		
	Mid Term Seminar/Presentation/ Class		SEE			
	Exam	Assignment/Quiz/Test	Participation			
Marks:	15	10	5	70		
CLO1	5	-	-	15		
CLO2	5	2.5	-	20		
CLO3	5	2.5		20		
CLO4		5		15		

w.e.f. Session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc. Electronic Science				
Semester	Third				
Name of the Course	Nanoelectronics: Nano-CM	IOS & beyond			
Course Code	M24-ELE-309				
Course Type	DEC-2				
Level of the course	500-599				
Pre-requisite for the course	MOS Devices and CMOS Circuits				
Course Learning Outcomes (CLO)	CLO 1 : Understand various issues related to nanoscale electronic devices.				
After completing this course, the learner will be able to:					
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30	0	30		
End Term Exam Marks	70 0 70				
Max. Marks	100 0 100				
Examination Time	3 hours				

<u>Instructions for Paper- Setter:</u> The examiner will set 9 questions asking two questions from each unit and one compulsory question by taking course learning outcomes (CLOs) into consideration. The compulsory question (Question No. 1) will consist at least 4 parts covering entire syllabus. The examinee will be required to attempt 5 questions, selecting one question from each unit and the compulsory question. All questions will carry equal marks.

Unit	Topics	Contact	CLOs
		Hours	
I	Overview of progress of microelectronics worldwide. International technology roadmap characteristics. Short channel MOS devices, CMOS scaling types; Constant field scaling, constant voltage scaling. Nanoscale MOSFET, FinFET, vertical MOSFETS's limits of CMOS technology.	15	CLO1
	Materials & processes for advanced sub 65nm CMOD technology.		
II	From microelectronics towards nanoelectronics. Noval approaches towards future devices. Introduction to nanotechnology and nanomaterials. Applications in different fields. Bottom up and top-down approaches	15	CLO2
III	Semiconductor Low dimensional systems- Two dimensional confinement of carriers, Quantum wells, One dimensional Quantum systems; quantum wires, Zero dimensional quantum structures: Quantum Dots.	16	CLO3
IV	Quantum devices: Resonant tunneling diode & transistor. Coulomb Blockade, Single Electron Transistor, Introduction to Spintronics, Material requirements for spintronics, Spin devices: Spin Transistor, Spin values etc.	14	CLO4
	Total Contact I	lours	60

Part C-Learning Resources

Recommended Books/e-resources/LMS:

1. Semicond"Nanoelectronics and Information Technology", (Advanced Electronic and Novel Devices), Waser Ranier, Wiley- VCH (2003)

- "The Physics of Low-dimensional Semiconductors". John H. Davies, Cambridge University Press, 1998.
- 3. "Introduction to Nano Technology", John Wiley & Sons, 2003.
- 4. "Introduction to Molecular Electronics", M.C. Petty, M.R.Bryce, and D.Bloor, Edward Arnold (1995).
- 5. "Quantum Hetrostructures", V.Mitin, V. Kochelap, and M.Stroscio, Cambridge University Press.

Outcomes	Internal Assessment (30 Marks)			End Semester Examination (70 Marks)
	Mid Term Seminar/Presentation/ Class		SEE	
	Exam	Assignment/Quiz/Test	Participation	
Marks:	15	10	5	70
CLO1	5	-	-	15
CLO2	5	2.5	-	20
CLO3	5	2.5		20
CLO4		5		15

w.e.f. Session: 2025-26					
	Part A - Introduction	n			
Name of Programme	M.Sc. Electronic Science				
Semester	Third				
Name of the Course	Emerging Memory Devices				
Course Code	M24-ELE-310				
Course Type	DEC-2				
Level of the course	500-599				
Pre-requisite for the course	NIL				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	CLO 2 : To study about architecture and operations of different				
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30	0	30		
End Term Exam Marks	70	70 0 70			
Max. Marks	100	0	100		
Examination Time	3 hours				

Unit	Topics	Contact	CLOs
		Hours	
	classification of memories		
- 1	Volatile Memories-1	15	CLO1
•	Static Random Access Memories (SRAMs): SRAM functionality:	13	0201
	architecture, timing diagrams, performance and timing specifications; SOI		
	SRAMs; SRAM cell structure- MOS SRAM architecture, MOS SRAM cell		
	and peripheral circuit operation, bipolar SRAM technologies, silicon on		
	insulator (SOI) SRAM, advanced SRAM architectures and technologies,		
	application specific SRAMs		
	Volatile Memories-2		
П	Dynamic Random Access Memories (DRAMs): DRAM technology	15	CLO2
"	development, CMOS CRAMs, 3-transistor DRAM; 1 transistor DRAM:	13	CLOZ
	functionality, architecture, timing diagrams, performance and timing		
	specifications; sense amplifier; word line driver; leakage mechanisms in a		
	DRAM; retention; retention time calculations.		
	Nonvolatile Memories		
Ш	FLASH memories; floating gate theory; structure and working of a SONOS	16	CLO3
111	cell; structure and working FLOTOX memories; multi-level flash memories;	10	CLOS
	NOR based flash memories; NAND based flash memories.		
	Non-silicon based Memories		

		PCRAM; Resistive RAM (RRAM), FeRAM; array device considerations for non-silicon based memories, Gallium Arsenide (GaAs) FRAMs, Analog memories: magnetoresistive random access memories (MRAMs), Experimental memory devices.		
	IV	Nonvolatile Memories: Masked Read, only memories (ROMs): High density ROMs, programmable read-only memories (PROMs)- bipolar PROMs, CMOS PROMs, erasable (UV)- Programmble read-only memories (EPROMs)- Floating Gate EPROM cell- one, time programmable (OTP) Eproms Electrically Erasable PROMs (EEPROMs), EEPROM technology and architecture, nonvolatile SRAM-Flash memories (EPROMs or EEPROM), Advanced flash memory architecture	14	CLO4
Ī		Total Contact H	lours	60

Recommended Books/e-resources/LMS:

- 7. Ashok K.Sharma, Semiconductor Memories Technology, testing and reliability, Prentice hall of India Private Limited, New Delhi 1997.
- 8. Ashok K Sharna, Advanced Semiconductor Memories Architecture, Design and Applications, Wiley 2002.
- 9. Anjan Ghosh, High Speed Semiconductor Devices, NPTEL Courseware, 2009.
- 10. W. D. Brown, and Joe Brewer, Nonvolatile Semiconductor Memory Technology: A Comprehensive Guide to Understanding and Using NVSM Devices, WileyIEEE Press, 1997.
- 11. J. Brewer, Nonvolatile Memory Technologies with Emphasis on Flash: A Comprehensive Guide to Understanding and Using Flash Memory Devices, Manzur Gill, Wiley-IEEE Press, 2008.

Evaluation Method						
Outcomes	Internal Assessment (30 Marks)			End Semester Examination (70 Marks)		
	Mid Term	Seminar/Presentation/	Class	SEE		
	Exam	Assignment/Quiz/Test	Participation			
Marks:	15	10	5	70		
CLO1	5	-	-	15		
CLO2	5	2.5	-	20		
CLO3	5	2.5		20		
CLO4		5		15		

	w.e.f. Session: 2	025-2	26	
	Part A - Introd	uctio	n	
Name of the Programme M.Sc Electronic Science				
Semester	Third			
Name of the Course	Electronic Communication	on Lal	0	
Course Code	M24-ELE-311			
Course Type	PC-5			
Level of the course	500-599			
Pre-requisite for the course (if any)				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to: CLO1: Familiarize with Simulation Tools, Test Benches used in designing of communication systems CLO2: Perform the simulation of electronic communication circuits. CLO3: Analyze & Interpret the data obtained in the experiments. CLO4: Present the experimental results and conclusions in the form of writted report in clear and concise manner.				
Credits	Theory		Practical	Total
	0		4	4
Teaching Hours per week	0		8	8
Internal Assessment Marks	0		30	30
End Term Exam Marks	0		70	70
Max. Marks	0		100	100
Examination Time	0		4 hours (or as decide	ed by PGBOS)
	Part B- Contents of	f the	Course	
	Part B- Contents o	fthe	Course	Contact Hours
 Digital Communication Digital Communication MATLAB Digital Communication 	Practicals riments. List may charairperson/staff councion-PCM using kit & Man-PWM using kit & Man-Delta Modulation usion-PPM using kit & Man-PPM	nge v l ATLA ATL ing k	AB/Octave AB/Octave it &	Contact Hours
per Cos with approval of characteristics. Digital Communication 2. Digital Communication 3. Digital Communication MATLAB Digital Communication MOSCAP fabrication	Practicals riments. List may charairperson/staff councion-PCM using kit & Man-PWM using kit & Man-Delta Modulation usion-PPM using kit & Man-PPM	nge v l ATLA ATLA ing k	vith every semester as AB/Octave AB/Octave it & AB etallization)	
per Cos with approval of characterization of c	Practicals riments. List may charairperson/staff councion-PCM using kit & Man-PWM using kit & Man-Delta Modulation usion-PPM using kit & Man-PPM	nge v l ATLA ATLA ing k	AB/Octave AB/Octave it &	
per Cos with approval of characterization of c	Practicals riments. List may charairperson/staff councion-PCM using kit & MAn-PWM using kit & Man-Delta Modulation usion-PPM using kit & MAN (Cleaning, oxidation around MOSCAP and extraction)	nge v l ATLA ATLA ing k ATLA ad ma	vith every semester as AB/Octave AB/Octave it & AB etallization)	
per Cos with approval of characterization of c	Practicals riments. List may charairperson/staff councion-PCM using kit & MAn-PWM using kit & Mon-Delta Modulation usion-PPM using kit & MAN-PPM	nge v I ATLA ATLA ing k ATLA ad ma	with every semester as AB/Octave AB/Octave it & AB etallization) n of various parameters	
per Cos with approval of characterization 1. Digital Communication 2. Digital Communication 3. Digital Communication MATLAB 4. Digital Communication 5. MOSCAP fabrication 6. CV characterization of from CV curve. 7. Microwave application	Practicals riments. List may charairperson/staff councin-PCM using kit & MA-n-PWM using kit & MA-n-Delta Modulation usin-PPM using kit & MA-(Cleaning, oxidation around the MOSCAP and extractions using Microwave be Suggested Evaluation	nge v I ATLA ATLA ing k ATLA ad ma	with every semester as AB/Octave AB/Octave it & AB etallization) n of various parameters	120
per Cos with approval of characterization 1. Digital Communication 2. Digital Communication 3. Digital Communication MATLAB 4. Digital Communication 5. MOSCAP fabrication 6. CV characterization of from CV curve. 7. Microwave application	Practicals riments. List may charairperson/staff councin-PCM using kit & MA-n-PWM using kit & MA-n-Delta Modulation usin-PPM using kit & MA-(Cleaning, oxidation around the MOSCAP and extractions using Microwave be Suggested Evaluation	nge v I ATLA ATLA ing k ATLA ind me actio nch nch	with every semester as AB/Octave AB/Octave it & AB etallization) n of various parameters ethods End Term Examin	120 ation: 70
per Cos with approval of characterization 1. Digital Communication 2. Digital Communication 3. Digital Communication MATLAB 4. Digital Communication 5. MOSCAP fabrication 6. CV characterization of from CV curve. 7. Microwave application Internal Assess Practicum	Practicals riments. List may charairperson/staff councin-PCM using kit & MA-n-PWM using kit & MA-n-Delta Modulation usin-PPM using kit & MA-(Cleaning, oxidation around the MOSCAP and extractions using Microwave be Suggested Evaluation	nge v l ATLA ATLA ing k ATLA ing caction	with every semester as AB/Octave AB/Octave it & AB etallization) n of various parameters ethods End Term Examin Practicum	120 ation: 70
per Cos with approval of characterization 1. Digital Communication 2. Digital Communication 3. Digital Communication MATLAB 4. Digital Communication 5. MOSCAP fabrication 6. CV characterization of from CV curve. 7. Microwave application Internal Assess Practicum Class Participation:	riments. List may charairperson/staff councin-PCM using kit & MAn-PWM using kit & MAn-PPM using kit & MAN-	nge v l ATLA ATLA ing k ATLA ind me actio nch on Me	with every semester as AB/Octave AB/Octave it & AB etallization) n of various parameters ethods End Term Examin Practicum Lab record, Viva-Voce, write	ation: 70 70 e-up and execution
per Cos with approval of characterization 1. Digital Communication 2. Digital Communication 3. Digital Communication MATLAB 4. Digital Communication 5. MOSCAP fabrication 6. CV characterization of from CV curve. 7. Microwave application Internal Assess Practicum	riments. List may charairperson/staff councin-PCM using kit & MAn-PWM using kit & MAn-PPM using kit & MAN-	nge v l ATLA ATLA ing k ATLA ing caction	with every semester as AB/Octave AB/Octave it & AB etallization) n of various parameters ethods End Term Examin Practicum	ation: 70 70 e-up and execution

Recommended Books/e-resources/LMS:

• Lab Manual of respective experiments

w.e.f. Session: 2025-26					
	Part A - Introduction				
Name of the Programme	M.Sc Electronic Science				
Semester	Third				
Name of the Course	EDA Tools for design & simulati	on			
Course Code	M24-ELE-312				
Course Type	PC-6				
Level of the course	500-599				
Pre-requisite for the course (if any)	NIL				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	Course Learning Outcomes (CLO) CLO1: Operate various CAD tools for designing and simulation of electroni systems CLO2: Write and execute the programs for embedded systems				
Credits	Theory	Practical	Total		
	0	4	4		
Teaching Hours per week	0	8	8		
Internal Assessment Marks	0	30	30		
End Term Exam Marks	End Term Exam Marks 0 70 70				
Max. Marks	0	100	100		
Examination Time 0 4 hours (or as decided by PGBOS)					

Part	B-	Cor	ntents	of the	Course

	practicals				
This	This is tentative list of experiments. List may change with every semester as				
per (per Cos with approval of chairperson/staff council				
	Section-A CAD Tools				
1.	VHDL/Verilog based behavioural design.	120			
2.	VHDL/Verilog based dataflow.				
3.	VHDL/Verilog Architectural design of digital circuits.				
4.	Synthesis of a digital circuit a demonstrating its working on FPGA / CPLD.				
5.	Device/Process simulation using Silvaco/open source simulator.				
6.	CMOS Inverter Design using Cadence/Backend				
	Section-B				
1.	a) Study of LPC2148 Microcontroller Architecture.				
	b) Familiarization with Tool.				
	c) Debug Practice with LPC2148 Kit				
	d) Write simple programs in Embedded C for LPC 2148.				
2.	Sine wave generation using microcontroller				
3.	Resistive (PT100) temp sensor interface with microcontroller.				

Suggested Evaluation Methods						
Internal Assessment: 30	End Term Examination: 70					
> Practicum	Practicum	70				
Class Participation:	5 Lab record, Viva-Voce, write-up and execu					
• Seminar/Demonstration/Viva-voce/Lab records etc.:	10	of the practical				
Mid-Term Exam:						

Recommended Books/e-resources/LMS:

• Lab manuals of respective experiments

w.e.f. Session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc. Electronic Science				
Semester	Fourth				
Name of the Course	VHDL for Digital Design				
Course Code	M24-ELE-401				
Course Type	DEC-3				
Level of the course	500-599				
Pre-requisite for the course	Digital circuits & system Design & Verilog Hardware Description Language				
After completing this course, the learner will be able to:	Course Learning Outcomes (CLO) CLO 1: Describe the basic concepts of VHDL language CLO 2: Classify behavior level modeling After completing this course, the CLO 3: Demonstrate data flow level modeling and Structural				
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30	0	30		
End Term Exam Marks	70 0 70				
Max. Marks	100	0	100		
Examination Time 3 hours					

Unit	Topics	Contact	CLOs
		Hours	
	Introduction to VHDL		
I	Basic Terminology, Entity declaration, Architectural Body, Configuration Declaration, Package Declaration, Package Body, Identifiers, Data Objects, Data Types, Operators	15	CLO1
II	Behavioral Modeling Process Statement, Variable Assignment Statement, Signal Assignment Statement, wait statement, if statement, case statement, null statement, loop statement, next statement, Assertion statement, Delay models, Other Sequential Statements, multiple process statement, Simulation: Writing a Test bench.	15	CLO2
	Dataflow Modeling		
III	Concurrent Signal Assignment, Concurrent versus sequential signal Assignment Statement, Conditional Signal Assignment statement, selected signal assignment statement. Structural Modeling: Component Declaration, Component Instantiation, Examples	16	CLO3
IV	Combinational Logic design using VHDL Decoders, encoders, priority encoder, multiplexers and demultiplexers, Code Converters, Parity circuits, comparators, Adders & subtractors, ALUs.	14	CLO4
	Sequential Logic design using VHDL Latches and flip-flops, counters, shift registers, Modeling Moore FSM, Modeling Mealy FSM Design.		
	Total Contact I	Hours	60

Recommended Books/e-resources/LMS:

- 1. J.Bhasker, "VHDL Primer", Pearson Education/PHI, 2015
- 2. John F. Wakerly, "Digital Design Principles & Practices", PHI/Pearson Education Asia, 3rd Ed., 2005.

Evaluation Michiga					
Outcomes	Internal Assessment			End Semester	
	(30 Marks)			Examination (70 Marks)	
	Mid Term	Seminar/Presentation/	Class	SEE	
	Exam	Assignment/Quiz/Test	Participation		
Marks:	15	10	5	70	
CLO1	5	-	-	15	
CLO2	5	2.5	-	20	
CLO3	5	2.5		20	
CLO4		5		15	

Session: 2025-26						
	Part A - Introduction					
Name of Programme	M.Sc Electronic Science					
Semester	Fourth					
Name of the Course	System Verilog					
Course Code	M24-ELE-402					
Course Type	DEC-3					
Level of the course	Level of the course 500-599					
Pre-requisite for the course (if any)	Digital Design, Verilog					
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	CLO 1:Ability to understand need and applications of SystemVerilog CLO 2:Ability to Understand the syntax of System Verilog CLO 3:Ability to understand different design methods using SystemVerilog CLO 4: Ability to design complex systems using SystemVerilog					
Credits	Theory	Practical	Total			
	4	0	4			
Teaching Hours per week	4	0	4			
Internal Assessment Marks	30	0	30			
End Term Exam Marks	70	0	70			
Max. Marks	100	0	100			
Examination Time	3 hours					

Unit	Topics	Contact Hours	CLOs
I	An introduction to gate-Level Design Using System Verilog	15	CLO1
	Important rules for using an HDL, Lvels of Design Abstraction, Basic		
	Structural System Verilog Design, Declaring wires in system Verilog,		
	CAD tool design flow.		
	Creating hierarchy via structural Instantiation, specifying constants in		
	system Verilog, accessing bits of multi-bit wire, naming modules,		
	wiresand instance names, hierarchial design flow		
II	Dataflow SystemVerilog	15	CLO2
	A Basic 2:1 MUX, Dataflow Operators, a 2:4 Decoder, Parameterization in		
	Dataflow SystemVerilog, SystemVerilog and Arithmetic.		
	Behavioral SystemVerilog for Registers		
	Introduction to Behavioral SystemVerilog, The always ff Block, Shift		
	Register Design Using Behavioral SystemVerilog, The Semantics of		
	the always ff Block,Reset Problems With Registers		
III	Behavioral SystemVerilog for Combinational Logic	15	CLO3
	Combinational always Blocks		
	The Use of case Statements in always comb Blocks, The Problem		
	With Latches in always comb Blocks, Avoiding Latches When Using		
	case Statements, Mapping SystemVerilog Programs to a Specific		
	Technology		
	State Machine Design Using SystemVerilog		

Γ	•	SystemVerilog Features for Coding State ,The 2-Always Block State		
		Machine Coding ,Enumerated Types for Symbolic State Names ,The		
		always comb IFL/OFL Block ,State Machine Coding Styles .		
Ī	IV	Case Study: A Soda Machine Controller	15	CLO4
		Understand the Complete System Requirements and Organization,		
		Determine a System Architecture, Design the System Parts - Design		
		of the Timer Subsystem, Design of the Keypad Interface Subsystem		
		Design of the Central Control Subsystem ,Design of the , Design of		
		the Central Control Subsystem State Machine, A Complete and		
		Conflict-Free State, Implementing the State Machine Using		
		SystemVerilog ,Asynchronous Inputs and Glitch-Free Outputs		
		Case Study: Design of UART		
		UART protocol design, Designing UART, Design of UART		
		Transmitter and Receiver		
		SystemVerilog design for bus structure, SystemVerilog vs Verilog		
T		Total Contact Hours	60	

Recommended Books/e-resources/LMS:

- 1. "Designing Digital Systems With SystemVerilog" by Dr. Brent E. Nelson, (2018), Independently Published
- 2. "SystemVerilog for Design Second Edition: A Guide to Using SystemVerilog for Hardware Design and Modeling" by Stuart Sutherland, Simon Davidmann, Peter Flake, (2006), Springer-Verlag New York Inc
- 3. "Introduction to SystemVerilog" by Ashok K. Mehta, (2021), Springer Nature Switzerland AG

Outcomes		Internal Assessment (30 Marks)		End Semester Examination (70 Marks)
	Mid Term Exam	Seminar/Presentation/ Assignment/Quiz/Test	Class Participation	SEE
Marks:	15	10	5	70
CLO1	5	2.5	_	17
CLO2	5	2.5	-	17
CLO3	2.5	2.5		18
CLO4	2.5	2.5		18

w.e.f. Session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc. Electronic Science				
Semester	Fourth				
Name of the Course	Design for Testability				
Course Code	M24-ELE-403				
Course Type	DEC-3				
Level of the course	500-599				
Pre-requisite for the course	Digital circuits & system Design				
	& Verilog Hardware Description Language				
Course Learning Outcomes (CLO)		undamentals of Design for Tes			
		ased Testing and Fault Analys			
After completing this course, the		es and Standards in Testabilit	y		
learner will be able to:	CLO 4: understand the E	merging trends in DFT			
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30 0 30				
End Term Exam Marks	70	0	70		
Max. Marks	100	0	100		
Examination Time	3 hours				

Unit	Topics	Contact	CLOs
		Hours	
	Introduction to Design for Testability: Importance in modern electronic		
1	systems, Historical background and evolution, Key concepts: Fault models,	15	CLO1
	testing methodologies, and standards		
	Built-In Self-Test (BIST) Techniques: Principles and architecture of BIST,		
	Benefits and limitations, BIST simulations and practical exercises		
	Scan-Based Testing and Fault Analysis: Scan Chains and Serial Testing:		
II	Design and use of scan chains, Optimization techniques for better coverage,	15	CLO2
"	Design and test of scan chains	13	CLOZ
	Fault Modeling and Simulation: Types of faults (stuck-at, bridging, etc.),		
	Simulation tools and fault coverage analysis, Fault simulation exercises		
	using CAD tools		
	Design for Testability (DFT) Strategies: Techniques for enhancing		
III	testability, Real-world case studies and successful implementations, DFT-	16	CLO3
'''	aware circuit design and testing Industry	10	CLOS
	Standards in Testability: Overview of IEEE standards (e.g., 1149.1)		
	JTAG), Compliance, certification, and validation processes, Testing for		
	standard compliance		
	Advanced Topics in DFT: Emerging trends in DFT (e.g., AI in testing, low-		
IV	power DFT), Future challenges and opportunities	14	CLO4
	Total Contact I	Hours	60

Recommended Books/e-resources/LMS:

- 12. Tripathi, Suman. Advanced VLSI Design and Testability Issues. CRC Press, 2020.
- 13. Wang, Laung-Terng. VLSI Test Principles and Architectures. Morgan Kaufmann, 2006.
- 14. Huhn, Sebastian. Design for Testability, Debug and Reliability. Springer Nature, 2021.

Outcomes		Internal Assessment (30 Marks)		End Semester Examination (70 Marks)
	Mid Term	Seminar/Presentation/	Class	SEE
	Exam	Assignment/Quiz/Test	Participation	
Marks:	15	10	5	70
CLO1	5	-	-	15
CLO2	5	2.5	-	20
CLO3	5	2.5		20
CLO4		5		15

w.e.f. session: 2025-26				
Part A - Introduction				
Name of Programme	M.Sc Electronic Science			
Semester	Fourth			
Name of the Course	Programming for Electronics	using Python		
Course Code	M24-ELE-404			
Course Type	DEC-3			
Level of the course	500-599			
Pre-requisite for the NIL				
course (if any)				
Course Learning Outcomes	CLO 1: Ability to understan			
(CLO)	CLO 2: Ability to Understand the syntax of Python			
1 0	After completing this course, CLO 3: Ability use python to generate plots			
the learner will be able to:	CLO 4: Ability to write prog	gram in python to si	mulate a design	
Credits	Theory	Practical	Total	
	4	0	4	
Teaching Hours per week	4	0	4	
Internal Assessment Marks	30	0	30	
End Term Exam Marks	70	0	70	
Max. Marks	100	0	100	
Examination Time	3 hours			

Unit	Topics	Contact Hours	CLOs
I	Python and Engineering, Modular Programming, Introduction to python, Installation, Python as a calculator, Modules	15	CLO1
	Data Types		
	Introduction to various data types, Logical, Numeric, Sequences, Set		
	and Frozen Set, Mappings and Null object		
II	Operators	15	CLO2
	Introduction, Concepts of Variables, Assignment, Arithmetic and		
	Logical, Membership, Identity, Bitwise operators		
	Arrays		
	Introduction, Numpy, adarray, automatic creation of arrays,		
	Numerical ranges, broadcasting, indexing, slicing, masking,		
	copying, some basic operations		
III	Plotting	15	CLO3
	Introduction, Matpltolib, basic plots, histograms, bar charts, pie		
	charts, polar plots, subplots, saving a plot file, displaying on web		
	servers, working in object mode, logarithmic plots, contour plots, 3d		
	plots, other libraries		
IV	Functions and Loops	15	CLO4
	Introduction, defining functions, multi-input multi-output		
	functions, Local and global variables, concept of loops, file I?O		
	Total Contact Hours	60	

Recommended Books/e-resources/LMS:

- 1. "Introduction to Python-for Scientists and Engineers" by Sandeep Nagar (2006), Independently Published
- Course No. 6.189, MIT Opencourseware, A Gentle Introduction to Programming using Python, (<u>A Gentle Introduction to Programming Using Python | Electrical Engineering and Computer Science | MIT OpenCourseWare</u>)

Outcomes		Internal Assessment (30 Marks)		End Semester Examination (70 Marks)
	Mid Term Exam	Seminar/Presentation/ Assignment/Quiz/Test	Class Participation	SEE
Marks:	15	10	5	70
CLO1	5	2.5	-	17
CLO2	5	2.5	-	17
CLO3	2.5	2.5		18
CLO4	2.5	2.5		18

w.e.f. Session: 2025-26					
	Part A - Introduction	on			
Name of Programme M.Sc. Electronic Science					
Semester	Fourth				
Name of the Course	Advanced Materials for VL	SI			
Course Code	M24-ELE-405				
Course Type	DEC-4				
Level of the course	500-599				
Pre-requisite for the course	Knowledge of IC Fabrication Technology				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	CLO 1: Describe the requirements of cleanrooms for IC fabrication CLO 2: Implement the Silicon wafer cleaning process for device fabrication CLO 3: Design and simulate the fabrication processes required for IC fabrication CLO 4: Explain process integration flow for different IC fabrication technologies				
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30	0	30		
End Term Exam Marks	70	0	70		
Max. Marks	100	0	100		
Examination Time	3 hours				

Instructions for Paper- Setter: The examiner will set 9 questions asking two questions from each unit and one compulsory question by taking course learning outcomes (CLOs) into consideration. The compulsory question (Question No. 1) will consist at least 4 parts covering entire syllabus. The examinee will be required to attempt 5 questions, selecting one question from each unit and the compulsory question. All questions will carry equal marks.

Unit	Topics	Contact	CLOs
		Hours	
	Clean Room Technology, Clean Room Classifications, Design concepts, Clean Room		
I	Installations and Operations, Automation related facility systems, future trends.	15	CLO1
II	Wafer Cleaning Technology - Basic Concepts, Wet cleaning, Dry cleaning, Epitaxy, Fundamental Aspects, Conventional silicon epitaxy, low temperature, Epitaxy of silicon, selective epitaxial growth of Si, Characterization of epitaxial films.	15	CLO2
III	Process simulation, Introduction, Ion-implantation, Monte Carlo method, Diffusion and Oxidation, two-dimensional LOCOS simulation example, Epitaxy, Epitaxial doping model, Lithography, Optical projection lithography, Electron-beam lithography, Etching and deposition, future trends.	16	CLO3
IV	VLSI Process Integration, Fundamental considerations for IC Processing, building individual layer, integrating the process steps, miniaturizing VLSI circuits, NMOS IC technology, fabrication process sequence, special consideration for NMOS ICs, CMOS IC technology, Fabrication Process sequence, special considerations for CMOS ICs, MOS memory IC technology, dynamic memory, static memory, bipolar IC technology, fabrication process	14	CLO4
	sequence, special considerations for bipolar ICs, Self-aligned bipolar structures, Integrated injection logic, IC fabrication, process monitoring future trends.		
	Total Contact I	lours	60

Part C-Learning Resources

Recommended Books/e-resources/LMS:

- VLSI Technology by S.M.Sze.
 ULSI Technology by C.Y. Chang and S.M. Sze (McGraw Hill International)

Outcomes		Internal Assessment (30 Marks)		End Semester Examination (70 Marks)
	Mid Term	Seminar/Presentation/	Class	SEE
	Exam	Assignment/Quiz/Test	Participation	
Marks:	15	10	5	70
CLO1	5	-	-	15
CLO2	5	2.5	-	20
CLO3	5	2.5		20
CLO4		5		15

w.e.f. Session: 2025-26				
Part A - Introduction				
Name of Programme	M.Sc. Electronic Science			
Semester	Fourth			
Name of the Course	RF Microelectronics			
Course Code	M24-ELE-406			
Course Type	DEC-4			
Level of the course	500-599			
Pre-requisite for the course	NIL			
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	 CLO 1: Understand the concepts of RF microelectronic devices and components CLO 2: Develop essential design concepts of RF networks and microelectronic circuits CLO 3: Understand various techniques for RF noise theories and frequency conversion techniques CLO 4: Understand the concept of microwave Integrated circuits 			
Credits	Theory	Practical	Total	
	4	0	4	
Teaching Hours per week	4	0	4	
Internal Assessment Marks	30	0	30	
End Term Exam Marks	70	0	70	
Max. Marks	100	0	100	
Examination Time	3 hours			

Unit	Topics	Contact	CLOs
		Hours	
I	Importance of RF and wireless technology, IC design technology for RF circuits, RF Behavior of passive components, operation for passive components at RF Active RF Components, RF Diodes, RF BJTs, RF FET, HEMT Active RF component modelling, Transistor models,	15	CLO1
II	Circuit representation of two port RF / Microwave Networks, Low and high frequency parameters, Formulation and properties of s parameters, Shifting reference plans, Transmission matrix, Generalized scattering parameters, Passive Circuit design, Review of Smith chart Matching and Biasing networks, Impedence matching using discrete components, microstrip line matching networks, amplifier classes of operation, RF Transistor amplifier designs, Low Noise amplifiers, Stability consideration, Constant gain noise figure circles	15	CLO2
III	Noise considerations in active networks, Noise definition, noise sources. RF Microwave oscillator design, Oscillator versus amplifier design, Oscillation conditions, Design of transistor oscillators, Generator Tuning networks RF / Microwave Frequency conversion II: Mixer design, Mixer types, Conversion loss for SSB mixers, SSB mixer versus DSB mixers. One diode mixers, Two diode mixers, Four diode mixers, Eight diode mixers,	16	CLO3
	Frequency synthesizers, PLL, RF synthesizer architectures, Transceiver architectures, Receiver architectures, Transmitter architectures, RF /		

IV	Microwave IC design, Microwave ICs, MIC Materials, Types of MICs, Hybrid vs monolithic MICs, Case studies, Relating to design of different circuits applicated in DE Microelectronics.		CLO4
	circuits employed in RF Microelectronics Total Contact	Hours	60

Recommended Books/e-resources/LMS:

- 15. Behzad Razavi, "RF Microelectronics" Prentice Hall PTR, 1998 16. R.Ludwig, P.Bretchko, RF Circuit Design, Pearson Education Asia, 2000.
- 17. Matthew M. Radmanesh, Radio Frequency and Microwave Electronics Illustrated, Pearson Education (Asia) Ltd., 2001

Outcomes	Internal Assessment (30 Marks)		End Semester Examination (70 Marks)	
	Mid Term	Seminar/Presentation/	Class	SEE
	Exam	Assignment/Quiz/Test	Participation	
Marks:	15	10	5	70
CLO1	5	-	-	15
CLO2	5	2.5	-	20
CLO3	5	2.5		20
CLO4		5		15

w.e.f. Session: 2025-26			
Part A - Introduction			
Name of Programme	M.Sc. Electronic Science		
Semester	Fourth		
Name of the Course	Nanoscience and Nanotec	chnology	
Course Code	M24-ELE-407		
Course Type	DEC-4		
Level of the course	500-599		
Pre-requisite for the course	NIL		
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	CLO1: Understand the basic concepts of Nanoscience and technology CLO2: Uunderstand the synthesis of nanomaterials CLO3: Characterize the nanomaterials CLO4: explain the aapplications of Nanoscience and Nanotechnology		
Credits	Theory 4	Practical 0	Total 4
Teaching Hours per week	4	0	4
Internal Assessment Marks	30	0	30
End Term Exam Marks	70	0	70
Max. Marks	100 0 100		
Examination Time	3 hours		

Unit	Topics	Contact	CLOs
		Hours	
	Basic concepts of Nanoscience and technology: Historical development of nanomaterials, Molecular and crystalline		
I	structures- Bulk to surface transition and calculations, density of states,	15	CLO1
	bandgap and dimensionality of nanomaterials, surface reconstruction,		
	Properties and technological advantages of Nano materials,		
	Nanostructures: Quantum wire, Quantum well, Quantum dot, Size		
	Effects, Quantum confinement, Fraction of Surface Atoms, specific		
	Surface Energy and Surface Stress, Effect on the Lattice Parameters.		
II	Processing of Nanomaterials: Chemical methods: Chemical reduction method, Colloids in solution, Langmuir-Blodgett (L-B) method, sol gel methods. Physical Methods: laser deposition. Physical Vapour deposition, hydrothermal/solvothermal methods, and Microwave Synthesis of materials. electrochemical methods.	15	CLO2
	Characterization of Nanomaterials:		
III	Structural Characterization: Powder X-ray diffractometer, FTIR spectrometer – Raman Spectrometer - Stylus profilometer. Microscopic and	15	CLO3

Hours	Total Contact	6	0
IV	Applications of Nanoscience and Nanotechnology Energy conservation and storage, Nanoelectronic devices, semiconductor nanodevices, solar cells, environmental remediation through nanoparticles, Nanoporous polymers and their applications in water purification, Biomedical Nanotechnology, Nanotechnology in Agriculture - Precision farming, Nanofertilizers-Nanourea and mixed fertilizers, Nanopesticides, Nanoseed Science. Nanotechnology in Food industry – Nanopackaging for enhanced shelf life.	15	CLO4
	Surface Analysis Electron microscopes: scanning electron microscope (SEM), transmission electron microscope (TEM); Scanning Probe Microscopy: atomic force microscope (AFM), scanning tunnelling microscope (STM). Electrical Properties: Impedance Spectroscopy, Thermal and Optical Properties: Differential scanning calorimeter (DSC)- Thermogravimetric/Diffferential thermal analyzer (TG/DTA), UV-Visible spectrophotometer.		

Recommended Books/e-resources/LMS:

- 1. The Chemistry of Nanomaterials: Synthesis, Properties and Applications, 2 Volume Set C. N. R. Rao (Editor), Achim Müller (Editor), Anthony K. Cheetham (Editor), 2004. Wiley Publisher.
- 2. Nanobiotechnology: Concepts, Applications and Perspectives, Christof M. Niemeyer (Editor), Chad A. Mirkin (Editor), Wiley Publishers, April 2004.
- 3. Nanotechnology: A Gentle Introduction to Next Big Idea, Mark Ratner and Daniel Ratner, Low Price edition, Third Impression, Pearson Education.
- 4. Zhong Lin Wang, Characterization of Nanophase Materials, Wiley-VCH, Verlag GmbH, Germany (2004).
- 5. Carl C. Koch, Nanostructured Materials: Processing, Properties and Potential Applications, Noyes Publications, William Andrew Publishing Norwich, New York, U.S.A (2002).
 - 1. Hari Singh Nalwa, "Nanostructured Materials and Nanotechnology", Academic Press, 2002
 - 2. Nanoparticles: From theory to applications G. Schmidt, Wiley Weinheim, 2004

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Outcomes	Internal Assessment			End Semester Examination (70 Marks)		
		(30 Marks)		(70 Marks)		
	Mid	Seminar/Presentation/	Class	SEE		
	Term	Assignment/Quiz/Test	Participation			
	Exam					
Marks:	15	10	5	70		
CLO1	7.5	-	-	17		
CLO2	7.5		-	17		
CLO3		5		18		
CLO4		5		18		

w.e.f. Session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc. Electronic Science				
Semester	Fourth				
Name of the Course	Semiconductor Packaging:	Technology & Materials			
Course Code	M24-ELE-408				
Course Type	DEC-4				
Level of the course	500-599				
Pre-requisite for the course	Knowledge of IC Fabrication Technology				
Course Learning Outcomes (CLO)					
After completing this course, the learner will be able to:	types CLO 3 : Explain the thern CLO 4: Compare the vari	nal issues in the IC packages ous packaging strategies			
Credits	Theory	Practical	Total		
4 0					
Teaching Hours per week	g Hours per week 4 0 4				
Internal Assessment Marks	30 0 30				
End Term Exam Marks	70 0 70				
Max. Marks	100	0	100		
Examination Time 3 hours					

<u>Instructions for Paper- Setter:</u> The examiner will set 9 questions asking two questions from each unit and one compulsory question by taking course learning outcomes (CLOs) into consideration. The compulsory question (Question No. 1) will consist at least 4 parts covering entire syllabus. The examinee will be required to attempt 5 questions, selecting one question from each unit and the compulsory question. All questions will carry equal marks.

Unit	Topics	Contact	CLOs
		Hours	
I	Introduction to IC Packaging Technologies: Significance and role of packaging in electronics, Historical evolution of packaging technologies, Packaging types: Through-hole, Surface-Mount, Ball Grid Array (BGA)	15	CLO1
II	Packaging Materials and Interconnection Techniques: Materials used in semiconductor packaging, Wire bonding, flip-chip, and solder bump technologies	15	CLO2
III	Thermal Management in IC Packaging: Principles of thermal conduction and dissipation, Cooling methods and heat sink strategies,	16	CLO3
IV	Packaging Types and Trade-offs: Comparative analysis: Through-hole, SMT, and BGA, Mechanical, electrical, and thermal trade-offs	14	CLO4
	Total Contact I	lours	60

Part C-Learning Resources

Recommended Books/e-resources/LMS:

- 18. 1. John H. Lau. Semiconductor Advanced Packaging. Springer, 2021.
- 19. King-Ning Tu, Chih Chen, Hung-Ming Chen. Electronic Packaging Science and Technology. Wiley, 2022.

Evaluation inclined						
Outcomes	Internal Assessment			End Semester		
		(30 Marks)		Examination (70 Marks)		
	Mid Term	Seminar/Presentation/	Class	SEE		
	Exam	Assignment/Quiz/Test	Participation			
Marks:	15	10	5	70		
CLO1	5	-	-	15		
CLO2	5	2.5	-	20		
CLO3	5	2.5		20		
CLO4		5		15		

w.e.f. session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc Electronic Science				
Semester	Fourth				
Name of the Course	Introduction to IOT				
Course Code	M24-ELE-409				
Course Type	DEC-5				
Level of the course	500-599				
Pre-requisite for the course (if any)	NONE				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to: CLO 1: Ability to understand need and applications of the IOT CLO 2: Ability to Understand the various components of IOT CLO 3: Ability to understand various Technologies Associated with IOT CLO 4: Ability to Understand the IOT topologies					
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week					
Internal Assessment 30 0 30 Marks					
End Term Exam Marks	End Term Exam Marks 70 0 70				
Max. Marks	100	0	100		
Examination Time	3 hours				

Instructions for Paper- Setter: The examiner will set 9 questions asking two questions from each unit and one compulsory question by taking course learning outcomes (CLOs) into consideration. The compulsory question (Question No. 1) will consist at least 4 parts covering entire syllabus. The examinee will be required to attempt 5 questions, selecting one question from each unit and the compulsory question. All questions will carry equal marks.

Unit	Topics	Contact	CLOs
		Hours	
I	Unit I	15	CLO1
	Basics of Networking: Introduction, Network Types, Layered		
	Network Models, Addressing, TCP/IP Transport layer		
	Basics of Network Security: Introduction, Security, Network		
	Confidentiality, Cryptography, Message Integrity and Authencity, Key		
	Management, Internet Security, Firewall		
II	Brief about predecessor of IOT, Introduction and Evolution of	15	CLO2
	IOT, Enabling IOT, IOT Networking Components, Addressing		
	Strategies in IOT		
III	IOT sensing and actuation: Sensor and actuator characteristics, Sensor and Actuator Types	15	CLO3
	IOT Processing Topologies and Types: Data format, Processing Toplologies, IOT Design and Selection Considerations, Processing Offloading, IOT connectivity and Communication Technologies		
IV	Associate IOT Technologies : Cloud Computing, Fog Computing	15	CLO4
	Cloud Computing: Introduction, Virtualisation, Cloud Model, SLA,		
	Cloud implementation		
	Fog Computing: Introduction, Architecture, Fog Computing in IOT		
	Case study of Agricultural, Vehicular and Healthcare IOT		
	Total Contact Hours	60)

Recommended Books/e-resources/LMS:

- 1. S. Misra, A. Mukherjee, and A. Roy, 2020. *Introduction to IoT*. Cambridge University Press
- 2. S. Misra, C. Roy, and A. Mukherjee, 2020. *Introduction to Industrial Internet of Things and Industry 4.0.* CRC Press.

Outcomes		Internal Assessment		End Semester Examination
o accornes		(30 Marks)		(70 Marks)
	Mid	Seminar/Presentation/	Class	SEE
	Term	Assignment/Quiz/Test	Participation	
	Exam	-		
Marks:	15	10	5	70
CLO1	5	2.5	-	17
CLO2	5	2.5	-	17
CLO3	2.5	2.5		18
CLO4	2.5	2.5		18

w.e.f. Session: 2025-26				
Part A – Introduction				
Name of Programme	M.Sc. Electronic Science			
Semester	Fourth			
Name of the Course	Optical Fiber Communication			
Course Code	M24-ELE-410			
Course Type	DEC-5			
Level of the course	500-599			
Pre-requisite for the course	NIL			
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	CO1: Understand the basic communication systems, principals and applications of optical fibers. CO2: Explain the dispersion and attenuation in optical fibers CO3: Understand various laser and LED structures and their characteristics, efficiency and reliability CO4: Explain the modulation and demodulation of Optical fiber systems & future developments			
Credits	Theory	Practical	Total	
T 1' II 1	4	0	4	
Teaching Hours per week	4	0	4	
Internal Assessment Marks End Term Exam Marks	30 0 30 70 0 70			
Max. Marks	70 100	0	100	
Examination Time	3 hours	U	100	

<u>Instructions for Paper- Setter:</u> The examiner will set 9 questions asking two questions from each unit and one compulsory question by taking course learning outcomes (CLOs) into consideration. The compulsory question (Question No. 1) will consist at least 4 parts covering entire syllabus. The examinee will be required to attempt 5 questions, selecting one question from each unit and the compulsory question. All questions will carry equal marks.

Unit	Topics	Contact Hours	CLOs
I	Optical communication, Introduction, the measurement of information & capacity of a telecommunication channel, communication system architecture, the basic communication system, Optical communication system, the economic merits, optical fibers digital telecommunication system, analogue system, application & future developments, optical satellite communication.	15	CLO1
II	Elementary discussion of propagation in Fibers, Propagation a ray model, signal degradation in optical fibers, Material dispersion, the combined effect of material dispersion & multipath dispersion, RMS pulse widths & frequency response, attenuation in optical fibers, attenuation mechanisms, assessment of silica fibers & cables, power launching and coupling, fiber connectors, splices & couples.	15	CLO2
III	Semiconductor lasers for optical communication, the development of stripe geometry lasers, direct modulation of Semiconductor lasers, optical & electrical characterization of stripe geometry, sources for longer	15	CLO3

	wavelength LED's efficiency of DHLED. LED structures, characteristics, reliability.		
IV	Optical fiber systems, intensity modulation/direct detection, the optical transmitter circuit, the optical receiver circuit, digital systems, planning consideration, analog system, coherent optical fiber system, detection principles, modulation formats, Demodulation schemes, receiver sensitivities, optical fiber communication application & future developments.	15	CLO4
Hours	Total Contact	60	
nours			

Recommended Books/e-resources/LMS:

- 1. Optical fiber communications (Principle and Practice) 2nd edition-John M.Senior (Prentice Hall India Pvt.Ltd, New Delhi).
- 2. Optical Communication Systems Second edition-John Gowar (Prentice Hall India Pvt. Ltd, New Delhi).
- 3. Optical Fiber Communications Gerd Keiser (McGraw Hill International editions, Singapore).
- 4. Fundamental of optical fiber communication second edition-Michael K.Barnoski (Academic Press, Orlando).
- 5. Fiber Optic Communication Systems-Govind P.Agarwal (John Wiley & Sons, Singapore).

Outcomes		Internal Assessment	End Semester Examination			
		(30 Marks)		(70 Marks)		
	Mid Term	Seminar/Presentation/	Class	SEE		
	Exam	Assignment/Quiz/Test	Participation			
Marks:	15	10	5	70		
CLO1	7.5	-	-	17		
CLO2	7.5		-	17		
CLO3		5		18		
CLO4		5		18		

w.e.f. Session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc. Electronic Science				
Semester	Fourth				
Name of the Course	Mobile and data communic	ation			
Course Code	M24-ELE-411				
Course Type	DEC-5				
Level of the course	500-599				
Pre-requisite for the course	site for the course NIL				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	CO1: Understand the concepts of mobile telephone CO2: Understand cellular technologies like 4G, 5G etc. CO3: Explain the basics of Data Communications CO4: Understand network layer, transport layer and application layer of communication				
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4	0	4		
Internal Assessment Marks	30	0	30		
End Term Exam Marks	70	0	70		
Max. Marks	100	0	100		
Examination Time	3 hours				

<u>Instructions for Paper- Setter:</u> The examiner will set 9 questions asking two questions from each unit and one compulsory question by taking course learning outcomes (CLOs) into consideration. The compulsory question (Question No. 1) will consist at least 4 parts covering entire syllabus. The examinee will be required to attempt 5 questions, selecting one question from each unit and the compulsory question. All questions will carry equal marks.

Unit	Topics	Contact	CI O
		Hours	CLOs
I	Introduction, Mobile telephone Service, Cellular Telephone, Frequency reuse, Interference, Cell splitting, Sectoring, Segmentation and Dualisation, Cellular System Topology, Roaming and Hands offs, Cellular telephone network components, Cellular telephone call processing, Digital Cellular Telephone, SMS, GSM, GPRS, CDMA and EDGE architecture.	15	CLO1
II	Telecommunication Network management overview, Wireless Network fundamentals, OSI model layers, architecture, broadband systems. Introduction to Emerging technologies IP multimedia systems, GSM/CDMA, Wi-Fi, Wi-Max, Blue Tooth, 3G/4G &5G Next Gen. Networks (NGN), IP/ mobile TV	15	CLO2
III	Data Communications: Components, standards and organizations, Network Classification, Network Topologies; network protocol; layered network architecture; overview of OSI reference model; overview of TCP/IP protocol suite. Physical Layer: Cabling, Network Interface Card, Transmission Media Devices-Repeater, Hub, Bridge, Switch, Router, Gateway.	15	CLO3
	Data Networking: Virtual Circuits and Datagram approach, IP addressing methods -Subnetting; Routing Algorithms (adaptive and non-adaptive); Network Layer		
IV	(1.2.1. 1.2. 6), 1.2.188-1-1-1-1 (1.2.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1	15	CLO4

Recommended Books/e-resources/LMS:

- 1. Mobile Cellular Telecommunication: Analog and Digital Systems by W.C.Y Lee, Mc Graw-Hill.
- 2. Mobile Communications by Jochen Schiller, Pearson Education.
 - 3. Electronic Communications Systems by Wayne Tomasi, Pearson Education
 - 4. Rappaport. T.S., "Wireless communications", Pearson Education, 2003.
 - 5. Gordon L. Stuber, "Principles of Mobile Communication", Springer International Ltd., 2001.
 - 6. Andrea Goldsmith, Wireless Communications, Cambridge University Press, 2007.
 - 7. Future Developments in Telecommunication, J. Martin, Prentice Hall

Outcomes	Internal Assessment (30 Marks)			End Semester Examination (70 Marks)
	Mid	id Seminar/Presentation/ Class		SEE
	Term Exam	Assignment/Quiz/Test	Participation	
Marks:	15	10	5	70
CLO1	7.5	-	-	17
CLO2	7.5		-	17
CLO3		5		18
CLO4		5		18

w.e.f. Session: 2025-26					
Part A - Introduction					
Name of Programme	M.Sc. Electronic Science	M.Sc. Electronic Science			
Semester	Fourth				
Name of the Course	Verification Tools & Techno	ologies			
Course Code	M24-ELE-412				
Course Type	DEC-5				
Level of the course	500-599				
Pre-requisite for the course	NIL				
Course Learning Outcomes (CLO)	CLO 1 : understand the importance of verification in digital design CLO 2 : learn simulation tools for basic verification of digital				
After completing this course, the learner will be able to:	systems CLO 3: explain the formal verification processes CLO 4: use industry standard verification tools for digital verification				
Credits	Theory	Practical	Total		
	4	0	4		
Teaching Hours per week	4 0 4				
Internal Assessment Marks	30 0 30				
End Term Exam Marks	70 0 70				
Max. Marks	100	0	100		
Examination Time	3 hours				

<u>Instructions for Paper- Setter:</u> The examiner will set 9 questions asking two questions from each unit and one compulsory question by taking course learning outcomes (CLOs) into consideration. The compulsory question (Question No. 1) will consist at least 4 parts covering entire syllabus. The examinee will be required to attempt 5 questions, selecting one question from each unit and the compulsory question. All questions will carry equal marks.

Unit	Topics	Contact	CLOs
		Hours	
	Introduction to Verification in Digital Design: Importance of verification		
1	in the design lifecycle, Functional verification concepts and terminology,	15	CLO1
	Overview of simulation-based verification		
	Simulation Tools and Basic Verification Techniques:		ļ
П	Hands-on with tools like ModelSim and VCS, Writing testbenches,	15	CLO2
'	generating stimulus, analyzing output		0101
	Formal Verification Principles: Concepts of formal verification, model		
III	checking, and theorem proving, Comparison of formal vs. simulation	16	CLO3
'''	methods, formal verification on small hardware designs	10	CLOS
	Industry-Standard Verification Tools: Overview and comparison of tools		
IV	like Questa, VCS, JasperGold Functionalities such as coverage analysis,	14	CLO4
10	waveforms, and debugging	14	CLO4
	Total Contact I	Hours	60

Part C-Learning Resources

Recommended Books/e-resources/LMS:

- 20. Douglas Perry. Applied Formal Verification. McGraw Hill, 2005.
- 21. Graham Birtwistle. VLSI Specification, Verification and Synthesis. Springer, 2012.
- 22. Thomas Kropf. Introduction to Formal Hardware Verification. Springer, 2013.
- 23. Erik Seligman. Formal Verification. Elsevier, 2023.

Liviladion McCirou					
Outcomes	Internal Assessment		End Semester		
		(30 Marks)		Examination (70 Marks)	
	Mid Term	Seminar/Presentation/	Class	SEE	
	Exam	Assignment/Quiz/Test	Participation		
Marks:	15	10	5	70	
CLO1	5	-	-	15	
CLO2	5	2.5	-	20	
CLO3	5	2.5		20	
CLO4		5		15	

w.e.f. Session: 2025-26					
Part A – Introduction					
Name of Programme	M.Sc. Electronic Science				
Semester	Fourth				
Name of the Course	Research Ethics				
Course Code	M24-ELE-413				
Course Type	EEC				
Level of the course	500-599				
Pre-requisite for the course	NIL				
Course Learning Outcomes (CLO)	CO1: Understand the research ethics. CO2: Understand the scientific conduct in research.				
After completing this course, the learner will be able to:					
Credits	Theory	Practical	Total		
	2	0	2		
Teaching Hours per week	2	0	2		
Internal Assessment Marks	15 0 15				
End Term Exam Marks	35	0	35		
Max. Marks	50	0	50		
Examination Time	3 hours				

<u>Instructions for Paper- Setter:</u> The examiner will set 8 questions asking four questions from each unit by taking course learning outcomes (CLOs) into consideration. The examinee will be required to attempt 5 questions in all, selecting at least two questions from each unit. All questions will carry equal marks.

Unit	Topics	Contact Hours	CLOs
I	Ethics: definition, moral philosophy, nature of moral judgements and reactions, Research Ethics: Informed consent; Confidentiality and privacy. Record-Keeping. Ethics with respect to science and research	6	CLO1 CLO2
II	Intellectual honesty and research integrity: Intellectual Property Rights (IPR): Copyright, patents, trademarks; Ethical considerations in intellectual property; Salient features of Indian and international laws of IPR. Scientific Misconduct: Fabrication, falsification, plagiarism. misrepresentation; Duplicate publication, conflict of interest: Research mismanagement, biased reporting, Peer review manipulation, data theft, and misuse.	6	CLO3 CLO4
	Total Contact Hours	12	

Part C-Learning Resources

Recommended Books/e-resources/LMS:

- 1. Bird, A. (2006). Philosophy of Science. Routledge.
- 2. Chaddah, P. (2018) Ethics in Competitive Research: Do not get scooped; do not get plagiarised.
- 3. Deakin, L. (2014). Best practice guidelines on publishing ethics: A publisher's perspective.

Wiley.

- 4. Indian National Science Academy. 2019. Ethics in Science Education, Research and Governance.
- 2. Research ethics for social scientists: Between ethical conduct and regulatory compliance. Sage.
- 3. MacIntyre, A. (198). A short history of ethics. Routledge.

Evaluation Method						
Outcomes	Internal Assessment			End Semester Examination		
		(15 Marks)		(35 Marks)		
	Mid	Mid Seminar/Presentation/ Class		SEE		
	Term	Assignment/Quiz/Test	Participation			
	Exam					
Marks:	6	6	3	35		
CLO1	3	-	-	9		
CLO2	3		-	9		
CLO3		3		8		
CLO4		3		9		

Session: 2024-25				
Part A - Introduction				
Name of Programme	M.Sc. Electronic Science			
Semester	Fourth			
Name of the Course	Dissertation			
Course Code	M24-ELE-414			
Course Type	Dissertation/Project Work	Dissertation/Project Work		
Level of the course	500-599			
Pre-requisite for the course				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	 CO1: Ability to engage in independent study to research literature in the identified domain. CO2: Ability to identify the community that shall benefit through the solution to the identified engineering problem and demonstrate concern for environment. CO3: Ability to engage in independent study to identify the mathematical concepts, science concepts, engineering concepts and management principles necessary to solve the identified engineering problem CO4: Ability to analyze and interpret results of experiments conducted on the designed solution(s) to arrive at valid conclusions CO5: Ability to perform the budget analysis of the project through the utilization of resources (finance, power, area, bandwidth, weight, size, any other) CO6: Ability to engage in effective written communication through the project report, journal/poster presentation of the project work CO7: Ability to engage in effective oral communication through presentation and demonstration of the project work CO8: Ability to perform in the team, contribute to the team and mentor/lead the team 			
Credits	Theory	Practical	Total	
			12	
Teaching Hours per week				
Evaluation of Dissertation & End Term Exam Marks (Viva Voce)			300	
Max. Marks			300	
Examination Time	3 hours			

The student will undertake independent research on a chosen topic under faculty / Mentor supervision at and Industry/University or an R7D organization. The student will write a well structured dissertation that would reflect critical thinking, analytical depth, and scholarly engagement with primary and secondary text.

w.e.f. Session: 2025-26					
Part A – Introduction					
Name of Programme	M.Sc. Electronic Science	M.Sc. Electronic Science			
Semester	Third				
Name of the Course	Fundamentals of Nanoma	nterials			
Course Code	M24-OEC-313				
Course Type	OEC				
Level of the course	500-599				
Pre-requisite for the course	NIL				
Course Learning Outcomes (CLO) After completing this course, the learner will be able to:	CO1: Explain general concepts of Nanomaterials CO2: Synthesize nanomaterials CO3: Identify the phase using search peak analysis from XRD pattern CO4: Interpret the characterized results				
Credits	Theory	Practical	Total		
	2	0	2		
Teaching Hours per week	2	0	2		
Internal Assessment Marks	15 0 15				
End Term Exam Marks	35 0 35				
Max. Marks	50 0 50				
Examination Time 3 hours					

<u>Instructions for Paper- Setter:</u> The examiner will set 8 questions asking four questions from each unit by taking course learning outcomes (CLOs) into consideration. The examinee will be required to attempt 5 questions in all, selecting at least two questions from each unit. All questions will carry equal marks.

Unit	Topics	Contact Hours	CLOs
I	Basic concepts of Nano science and technology, Properties and technological advantages of Nano materials, Nanostructures: Quantum wire, Quantum well, Quantum dot, Size Effects, Quantum confinement, Fraction of Surface Atoms, specific Surface Energy and Surface Stress, Material processing by Sol – Gel method, Chemical Vapour deposition and Physical Vapour deposition, hydrothermal/solvothermal methods.	6	CLO1 CLO2
II	Experimental approaches and data interpretation: X ray characterization, Scanning probe microscope (AFM and STM), Electron microscopy: SEM/TEM, high resolution imaging, Differential scanning calorimeter (DSC) Thermogravimetric/Differential thermal analyzer (TG/DTA), UV-Visible spectrophotometer, FTIR	6	CLO3 CLO4
	Total Contact	12	
Hours			

Part C-Learning Resources

Recommended Books/e-resources/LMS:

1 C. N. R. Rao, A. Mu'ller, A. K. Cheetham, The Chemistry of Nanomaterials: Synthesis, Properties and Applications, Volume 1, Wiley-VCH, Verlag GmbH, Germany (2004).

- 2 C. Bre'chignac P. Houdy M. Lahmani, Nanomaterials and Nanochemistry, Springer Berlin Heidelberg, Germany (2006).
- 3 Guozhong Cao, Nanostructures & Nanomaterials Synthesis, Properties G;Z: Applications, World Scientific Publishing Private, Ltd., Singapore (2004).
- 4 Zhong Lin Wang, Characterization Of Nanophase Materials, Wiley-VCH, Verlag GmbH, Germany (2004). 5) Carl C. Koch, Nanostructured Materials: Processing, Properties and Potential Applications, Noyes Publications, William Andrew Publishing Norwich, New York, U.S.A (2002).
- 5. Hari Singh Nalwa, "Nanostructured Materials and Nanotechnology", Academic Press, 2002

Outcomes		Internal Assessme (15 Marks)	End Semester Examination (35 Marks)	
	Mid	Seminar/Presentation/	Class	SEE
	Term	Assignment/Quiz/Test	Participation	
	Exam			
Marks:	6	6	3	35
CLO1	3	-	-	9
CLO2	3		-	9
CLO3		3		8
CLO4		3		9